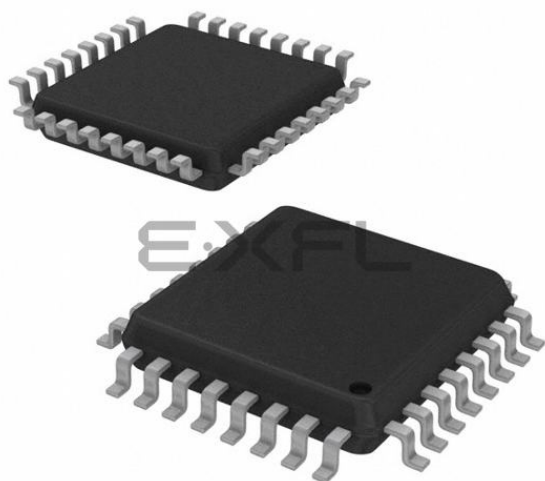




Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	25
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	6K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l071kbt6tr

	6.3.16	Temperature sensor characteristics	98
	6.3.17	Comparators	99
	6.3.18	Timer characteristics	100
	6.3.19	Communications interfaces	100
7		Package information	108
	7.1	LQFP100 package information	108
	7.2	UFBGA100 package information	111
	7.3	LQFP64 package information	113
	7.4	TFBGA64 package information	116
	7.5	WLCSP49 package information	119
	7.6	LQFP48 package information	122
	7.7	LQFP32 package information	125
	7.8	UFQFPN32 package information	128
	7.9	Thermal characteristics	131
	7.9.1	Reference document	132
8		Part numbering	133
9		Revision history	134

List of figures

Figure 1.	STM32L071xx block diagram	12
Figure 2.	Clock tree	23
Figure 3.	STM32L071xx LQFP100 pinout - 14 x 14 mm	33
Figure 4.	STM32L071xx UFBGA100 ballout - 7 x 7 mm	34
Figure 5.	STM32L071xx LQFP64 pinout - 10 x 10 mm	34
Figure 6.	STM32L071xx TFBGA64 ballout - 5 x 5 mm	35
Figure 7.	STM32L071xx WLCSP49 ballout	36
Figure 8.	STM32L071xx LQFP48 pinout - 7 x 7 mm	37
Figure 9.	STM32L071xx LQFP32 pinout	37
Figure 10.	STM32L071xx UFQFPN32 pinout	38
Figure 11.	Memory map	52
Figure 12.	Pin loading conditions	53
Figure 13.	Pin input voltage	53
Figure 14.	Power supply scheme	54
Figure 15.	Current consumption measurement scheme	54
Figure 16.	IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE, 1WS	63
Figure 17.	IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSI16, 1WS	63
Figure 18.	IDD vs VDD, at TA= 25 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS	67
Figure 19.	IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive	68
Figure 20.	IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks off	69
Figure 21.	High-speed external clock source AC timing diagram	75
Figure 22.	Low-speed external clock source AC timing diagram	76
Figure 23.	HSE oscillator circuit diagram	77
Figure 24.	Typical application with a 32.768 kHz crystal	78
Figure 25.	HSI16 minimum and maximum value versus temperature	79
Figure 26.	VIH/VIL versus VDD (CMOS I/Os)	89
Figure 27.	VIH/VIL versus VDD (TTL I/Os)	89
Figure 28.	I/O AC characteristics definition	92
Figure 29.	Recommended NRST pin protection	93
Figure 30.	ADC accuracy characteristics	96
Figure 31.	Typical connection diagram using the ADC	97
Figure 32.	Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})	97
Figure 33.	Power supply and reference decoupling (V_{REF+} connected to V_{DDA})	98
Figure 34.	SPI timing diagram - slave mode and CPHA = 0	104
Figure 35.	SPI timing diagram - slave mode and CPHA = 1 ⁽¹⁾	105
Figure 36.	SPI timing diagram - master mode ⁽¹⁾	105
Figure 37.	I ² S slave timing diagram (Philips protocol) ⁽¹⁾	107
Figure 38.	I ² S master timing diagram (Philips protocol) ⁽¹⁾	107
Figure 39.	LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline	108
Figure 40.	LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint	110
Figure 41.	LQFP100 marking example (package top view)	110
Figure 42.	UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball	

2.2 Ultra-low-power device continuum

The ultra-low-power family offers a large choice of core and features, from 8-bit proprietary core up to ARM® Cortex®-M4, including ARM® Cortex®-M3 and ARM® Cortex®-M0+. The STM32Lx series are the best choice to answer your needs in terms of ultra-low-power features. The STM32 ultra-low-power series are the best solution for applications such as gaz/water meter, keyboard/mouse or fitness and healthcare application. Several built-in features like LCD drivers, dual-bank memory, low-power run mode, operational amplifiers, 128-bit AES, DAC, crystal-less USB and many other definitely help you building a highly cost optimized application by reducing BOM cost. STMicroelectronics, as a reliable and long-term manufacturer, ensures as much as possible pin-to-pin compatibility between all STM8Lx and STM32Lx on one hand, and between all STM32Lx and STM32Fx on the other hand. Thanks to this unprecedented scalability, your legacy application can be upgraded to respond to the latest market feature and efficiency requirements.

- **Stop mode without RTC**

The Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are disabled.

Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 3.5 μ s, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on). It can also be wakened by the USART/I2C/LPUART/LPTIMER wakeup events.

- **Standby mode with RTC**

The Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSE crystal and HSI RC oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

The device exits Standby mode in 60 μ s when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

- **Standby mode without RTC**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

The device exits Standby mode in 60 μ s when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode.

Table 3. Functionalities depending on the operating power supply range

Operating power supply range	Functionalities depending on the operating power supply range		
	ADC operation	Dynamic voltage scaling range	I/O operation
$V_{DD} = 1.65$ to 1.71 V	ADC only, conversion time up to 570 ksps	Range 2 or range 3	Degraded speed performance
$V_{DD} = 1.71$ to 1.8 V ⁽¹⁾	ADC only, conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Degraded speed performance
$V_{DD} = 1.8$ to 2.0 V ⁽¹⁾	Conversion time up to 1.14 Msps	Range1, range 2 or range 3	Degraded speed performance

Only a 32.768 kHz clock (LSE) is needed to allow LPUART communication up to 9600 baud. Therefore, even in Stop mode, the LPUART can wait for an incoming frame while having an extremely low energy consumption. Higher speed clock can be used to reach higher baudrates.

LPUART interface can be served by the DMA controller.

3.15.4 Serial peripheral interface (SPI)/Inter-integrated sound (I2S)

Up to two SPIs are able to communicate at up to 16 Mb/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

The USARTs with synchronous capability can also be used as SPI master.

One standard I2S interfaces (multiplexed with SPI2) is available. It can operate in master or slave mode, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When the I2S interfaces is configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

The SPIs can be served by the DMA controller.

Refer to [Table 13](#) for the differences between SPI1 and SPI2.

Table 13. SPI/I2S implementation

SPI features ⁽¹⁾	SPI1	SPI2
Hardware CRC calculation	X	X
I2S mode	-	X
TI mode	X	X

1. X = supported.

3.16 Cyclic redundancy check (CRC) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

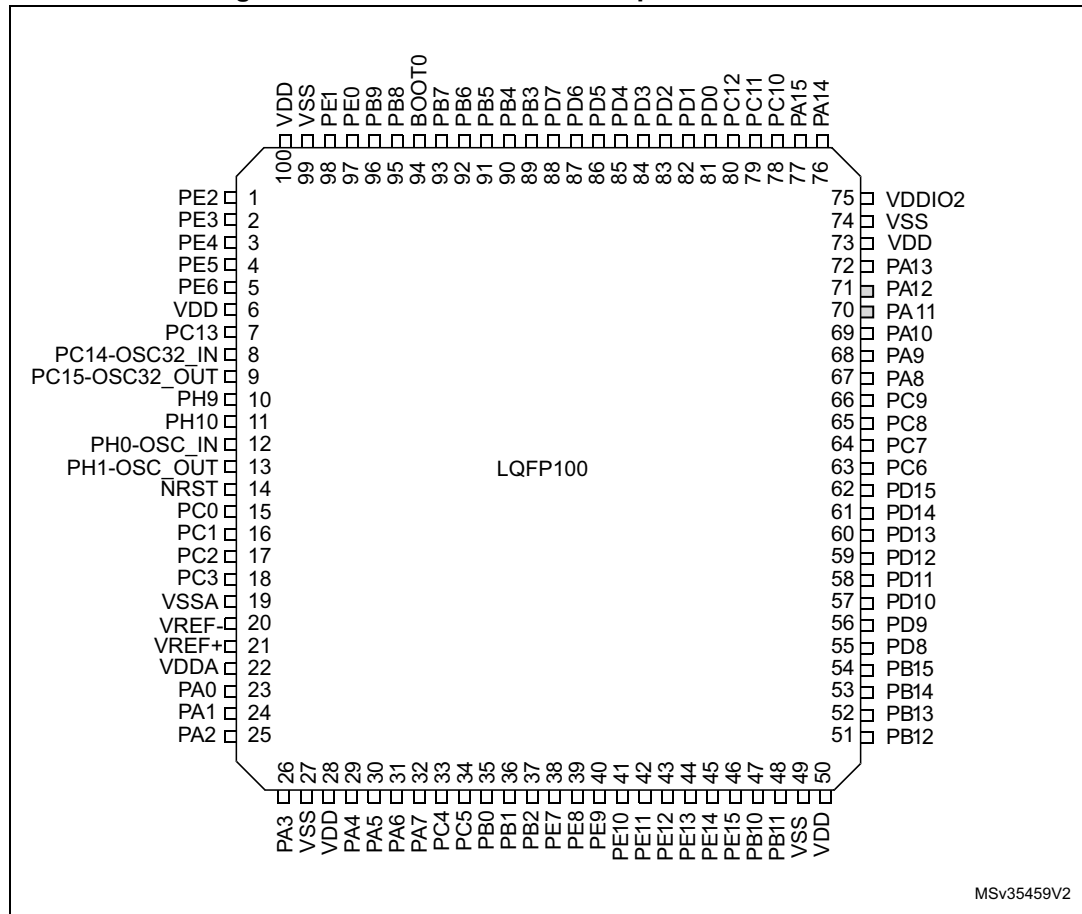
Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at linktime and stored at a given memory location.

3.17 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

4 Pin descriptions

Figure 3. STM32L071xx LQFP100 pinout - 14 x 14 mm



1. The above figure shows the package top view.
2. I/O supplied by VDDIO2.

Table 15. STM32L071xxx pin definition (continued)

Pin number								Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32 ⁽¹⁾	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100						
30	29	43	59	C3	C3	93	B4	PB7	I/O	FTf	-	USART1_RX, I2C1_SDA, LPTIM1_IN2, USART4_CTS	COMP2_INP, VREF_PVD_IN
31	30	44	60	B4	A5	94	A4	BOOT0	I		-	-	-
-	-	45	61	B3	B5	95	A3	PB8	I/O	FTf	-	I2C1_SCL	-
-	-	46	62	A3	A6	96	B3	PB9	I/O	FTf	-	EVENTOUT, I2C1_SDA, SPI2_NSS/I2S2_WS	-
-	-	-	-	-	-	97	C3	PE0	I/O	FT	-	EVENTOUT	-
-	-	-	-	-	-	98	A2	PE1	I/O	FT	-	EVENTOUT	-
32	31	47	63	D4	-	99	D3	VSS	S		-	-	-
-	32	48	64	E4	A7	100	C4	VDD	S		-	-	-

1. UFQFPN32 pinout differs from other STM32 devices except STM32L07xxx and STM32L8xxx.



Table 18. Alternate functions port C

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SPI1/SPI2/I2S2/ USART1/2/ LPUART1/ LPTIM1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2/I2C1/ TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/ LPTIM1/TIM2/3 /EVENTOUT/SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2 /I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/E VENTOUT	I2C3/LPUART1/ COMP1/2/ TIM3
Port C	PC0	LPTIM1_IN1		EVENTOUT				LPUART1_RX	I2C3_SCL
	PC1	LPTIM1_OUT		EVENTOUT				LPUART1_TX	I2C3_SDA
	PC2	LPTIM1_IN2		SPI2_MISO/ I2S2_MCK					
	PC3	LPTIM1_ETR		SPI2_MOSI/ I2S2_SD					
	PC4	EVENTOUT		LPUART1_TX					
	PC5			LPUART1_RX					
	PC6	TIM22_CH1		TIM3_CH1					
	PC7	TIM22_CH2		TIM3_CH2					
	PC8	TIM22_ETR		TIM3_CH3					
	PC9	TIM21_ETR		TIM3_CH4					I2C3_SDA
	PC10	LPUART1_TX						USART4_TX	
	PC11	LPUART1_RX						USART4_RX	
	PC12			USART5_TX				USART4_CK	
	PC13								
	PC14								
	PC15								

Table 21. Alternate functions port H

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SPI1/SPI2/ I2S2/USART1/2/ LPUART1/ LPTIM1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2 /I2C1/TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/ LPTIM1/TIM2/3/ EVENTOUT/ SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2/I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/ EVENTOUT	I2C3/ LPUART1/ COMP1/2/ TIM3
Port H	PH0		-	-	-	-	-	-	-
	PH1	-	-	-	-	-	-	-	-
	PH9	-	-	-	-	-	-	-	-
	PH10	-	-	-	-	-	-	-	-

Table 26. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	V
		Rising edge	3.08	3.15	3.20	
V_{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization results.

2. Valid for device version without BOR at power up. Please see option "D" in Ordering information scheme for more details.

6.3.3 Embedded internal reference voltage

The parameters given in [Table 28](#) are based on characterization results, unless otherwise specified.

Table 27. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C $V_{DDA} = 3\text{ V}$	0x1FF8 0078 - 0x1FF8 0079

Table 28. Embedded internal reference voltage⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{REFINT\ out}^{(2)}$	Internal reference voltage	$-40\text{ °C} < T_J < +125\text{ °C}$	1.202	1.224	1.242	V
$T_{VREFINT}$	Internal reference startup time	-	-	2	3	ms
V_{VREF_MEAS}	V_{DDA} and V_{REF+} voltage during V_{REFINT} factory measure	-	2.99	3	3.01	V
A_{VREF_MEAS}	Accuracy of factory-measured V_{REFINT} value ⁽³⁾	Including uncertainties due to ADC and V_{DDA}/V_{REF+} values	-	-	±5	mV
$T_{Coeff}^{(4)}$	Temperature coefficient	$-40\text{ °C} < T_J < +125\text{ °C}$	-	25	100	ppm/°C
$A_{Coeff}^{(4)}$	Long-term stability	1000 hours, $T = 25\text{ °C}$	-	-	1000	ppm
$V_{DDCcoeff}^{(4)}$	Voltage coefficient	$3.0\text{ V} < V_{DDA} < 3.6\text{ V}$	-	-	2000	ppm/V
$T_{S_vrefint}^{(4)(5)}$	ADC sampling time when reading the internal reference voltage	-	5	10	-	µs
$T_{ADC_BUF}^{(4)}$	Startup time of reference voltage buffer for ADC	-	-	-	10	µs
$I_{BUF_ADC}^{(4)}$	Consumption of reference voltage buffer for ADC	-	-	13.5	25	µA
$I_{VREF_OUT}^{(4)}$	VREF_OUT output current ⁽⁶⁾	-	-	-	1	µA
$C_{VREF_OUT}^{(4)}$	VREF_OUT output load	-	-	-	50	pF

Figure 18. I_{DD} vs V_{DD} , at $T_A = 25^\circ\text{C}$, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS

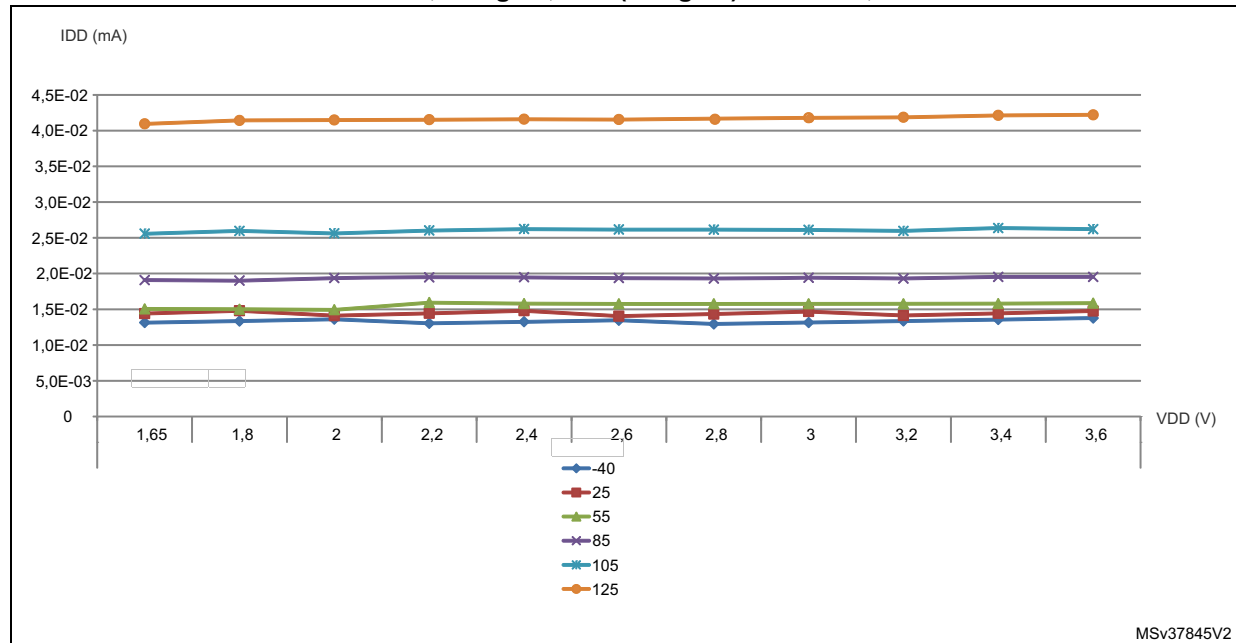


Table 35. Current consumption in Low-power sleep mode

Symbol	Parameter	Condition			Typ	Max (1)	Unit
I_{DD} (LP Sleep)	Supply current in Low-power sleep mode	All peripherals OFF, code executed from Flash memory, V_{DD} from 1.65 to 3.6 V	MSI clock = 65 kHz, $f_{HCLK} = 32$ kHz, Flash memory OFF	$T_A = -40$ to 25°C	4,7	-	μA
			MSI clock = 65 kHz, $f_{HCLK} = 32$ kHz	$T_A = -40$ to 25°C	17	24	
				$T_A = 85^\circ\text{C}$	19,5	30	
				$T_A = 105^\circ\text{C}$	23	47	
				$T_A = 125^\circ\text{C}$	32,5	70	
			MSI clock = 65 kHz, $f_{HCLK} = 65$ kHz	$T_A = -40$ to 25°C	17	24	
				$T_A = 85^\circ\text{C}$	20	31	
				$T_A = 105^\circ\text{C}$	23,5	47	
				$T_A = 125^\circ\text{C}$	32,5	70	
			MSI clock = 131kHz, $f_{HCLK} = 131$ kHz	$T_A = -40$ to 25°C	19,5	27	
				$T_A = 55^\circ\text{C}$	20,5	28	
				$T_A = 85^\circ\text{C}$	22,5	33	
				$T_A = 105^\circ\text{C}$	26	50	
				$T_A = 125^\circ\text{C}$	35	73	

1. Guaranteed by characterization results at 125°C , unless otherwise specified.

Table 36. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions	Typ	Max ⁽¹⁾	Unit
I_{DD} (Stop)	Supply current in Stop mode	$T_A = -40$ to 25°C	0,43	1,00	μA
		$T_A = 55^\circ\text{C}$	0,735	2,50	
		$T_A = 85^\circ\text{C}$	2,25	4,90	
		$T_A = 105^\circ\text{C}$	5,3	13,00	
		$T_A = 125^\circ\text{C}$	12,5	28,00	

1. Guaranteed by characterization results at 125°C , unless otherwise specified.

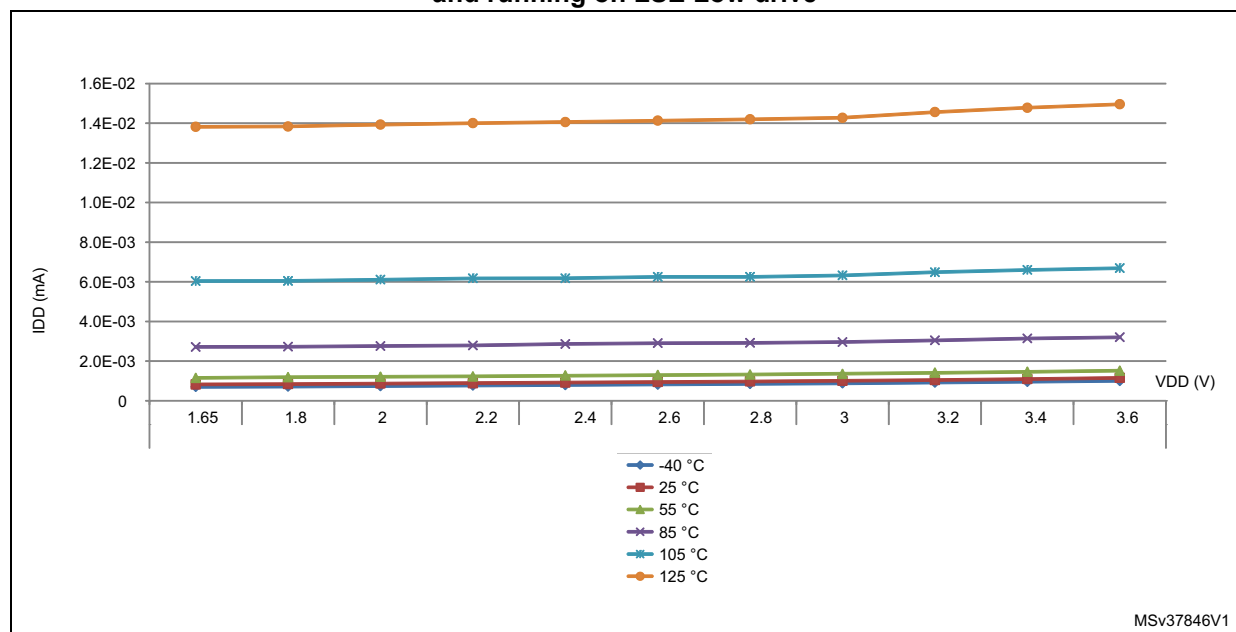
Figure 19. I_{DD} vs V_{DD} , at $T_A = 25/55/ 85/105/125^\circ\text{C}$, Stop mode with RTC enabled and running on LSE Low drive

Table 41. Low-power mode wakeup timings (continued)

Symbol	Parameter	Conditions	Typ	Max	Unit
t_{WUSTOP}	Wakeup from Stop mode, regulator in Run mode	$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$	5.0	8	μs
		$f_{HCLK} = f_{HSI} = 16 \text{ MHz}$	4.9	7	
		$f_{HCLK} = f_{HSI}/4 = 4 \text{ MHz}$	8.0	11	
	Wakeup from Stop mode, regulator in low-power mode	$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ Voltage range 1	5.0	8	
		$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ Voltage range 2	5.0	8	
		$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ Voltage range 3	5.0	8	
		$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	7.3	13	
		$f_{HCLK} = f_{MSI} = 1.05 \text{ MHz}$	13	23	
		$f_{HCLK} = f_{MSI} = 524 \text{ kHz}$	28	38	
		$f_{HCLK} = f_{MSI} = 262 \text{ kHz}$	51	65	
		$f_{HCLK} = f_{MSI} = 131 \text{ kHz}$	100	120	
		$f_{HCLK} = f_{MSI} = 65 \text{ kHz}$	190	260	
		$f_{HCLK} = f_{HSI} = 16 \text{ MHz}$	4.9	7	
		$f_{HCLK} = f_{HSI}/4 = 4 \text{ MHz}$	8.0	11	
	Wakeup from Stop mode, regulator in low-power mode, code running from RAM	$f_{HCLK} = f_{HSI} = 16 \text{ MHz}$	4.9	7	
		$f_{HCLK} = f_{HSI}/4 = 4 \text{ MHz}$	7.9	10	
		$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$	4.7	8	
$t_{WUSTDBY}$	Wakeup from Standby mode FWU bit = 1	$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	65	130	ms
	Wakeup from Standby mode FWU bit = 0	$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	2.2	3	

Table 51. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Typ	Max ⁽¹⁾	Unit
I _{DD}	Average current during the whole programming / erase operation	T _A = 25 °C, V _{DD} = 3.6 V	-	500	700	μA
	Maximum current (peak) during the whole programming / erase operation		-	1.5	2.5	mA

1. Guaranteed by design.

Table 52. Flash memory and data EEPROM endurance and retention

Symbol	Parameter	Conditions	Value	Unit
			Min ⁽¹⁾	
N _{CYC} ⁽²⁾	Cycling (erase / write) Program memory	T _A = -40°C to 105 °C	10	kcycles
	Cycling (erase / write) EEPROM data memory		100	
	Cycling (erase / write) Program memory	T _A = -40°C to 125 °C	0.2	
	Cycling (erase / write) EEPROM data memory		2	
t _{RET} ⁽²⁾	Data retention (program memory) after 10 kcycles at T _A = 85 °C	T _{RET} = +85 °C	30	years
	Data retention (EEPROM data memory) after 100 kcycles at T _A = 85 °C		30	
	Data retention (program memory) after 10 kcycles at T _A = 105 °C	T _{RET} = +105 °C	10	
	Data retention (EEPROM data memory) after 100 kcycles at T _A = 105 °C			
	Data retention (program memory) after 200 cycles at T _A = 125 °C	T _{RET} = +125 °C		
	Data retention (EEPROM data memory) after 2 kcycles at T _A = 125 °C			

1. Guaranteed by characterization results.

2. Characterization is done according to JEDEC JESD22-A117.

6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 54. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. frequency range at 32 MHz	Unit
S _{EMI}	Peak level	V _{DD} = 3.6 V, T _A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	-7	dBμV
			30 to 130 MHz	14	
			130 MHz to 1 GHz	9	
			EMI Level	2	-

6.3.17 Comparators

Table 67. Comparator 1 characteristics

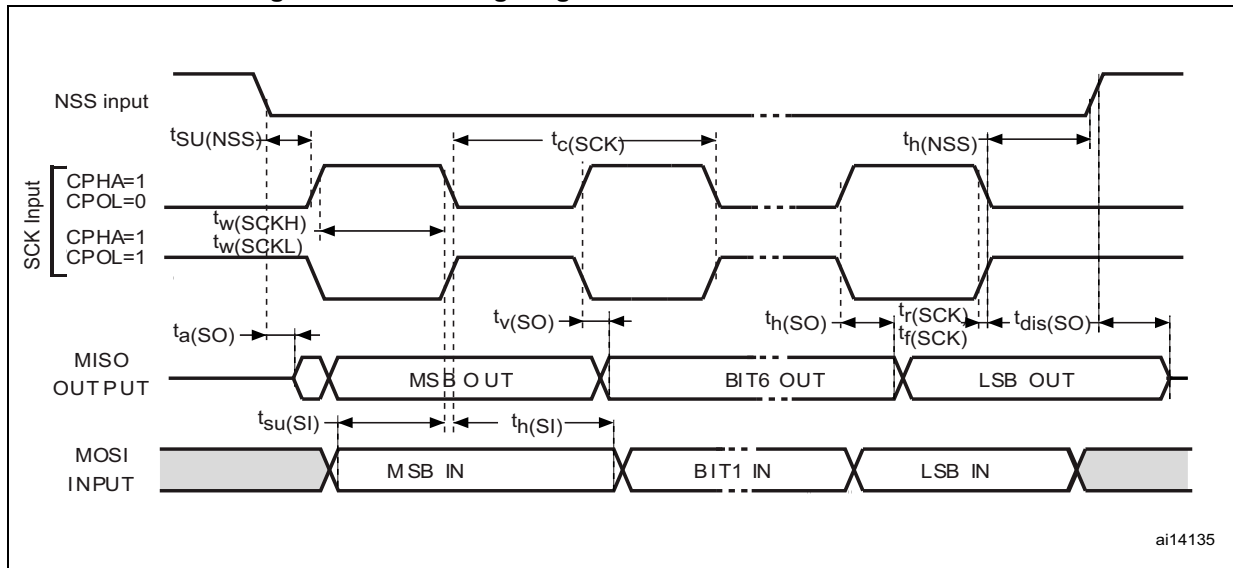
Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
V _{DDA}	Analog supply voltage	-	1.65		3.6	V
R _{400K}	R _{400K} value	-	-	400	-	kΩ
R _{10K}	R _{10K} value	-	-	10	-	
V _{IN}	Comparator 1 input voltage range	-	0.6	-	V _{DDA}	V
t _{START}	Comparator startup time	-	-	7	10	μs
t _d	Propagation delay ⁽²⁾	-	-	3	10	
V _{offset}	Comparator offset	-	-	±3	±10	mV
d _{Voffset} /dt	Comparator offset variation in worst voltage stress conditions	V _{DDA} = 3.6 V, V _{IN+} = 0 V, V _{IN-} = V _{REFINT} , T _A = 25 °C	0	1.5	10	mV/1000 h
I _{COMP1}	Current consumption ⁽³⁾	-	-	160	260	nA

1. Guaranteed by characterization.
2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
3. Comparator consumption only. Internal reference voltage not included.

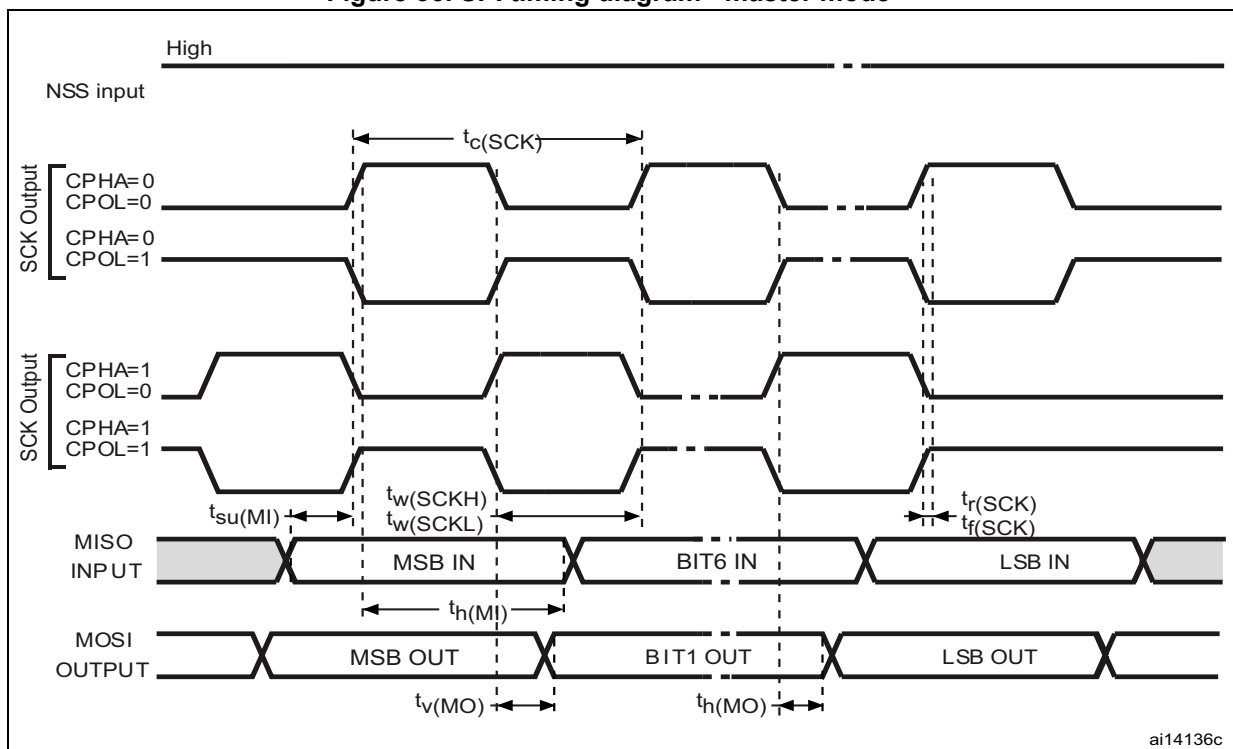
Table 68. Comparator 2 characteristics

Symbol	Parameter	Conditions	Min	Typ	Max ⁽¹⁾	Unit
V _{DDA}	Analog supply voltage	-	1.65	-	3.6	V
V _{IN}	Comparator 2 input voltage range	-	0	-	V _{DDA}	V
t _{START}	Comparator startup time	Fast mode	-	15	20	μs
		Slow mode	-	20	25	
t _{d slow}	Propagation delay ⁽²⁾ in slow mode	1.65 V ≤ V _{DDA} ≤ 2.7 V	-	1.8	3.5	
		2.7 V ≤ V _{DDA} ≤ 3.6 V	-	2.5	6	
t _{d fast}	Propagation delay ⁽²⁾ in fast mode	1.65 V ≤ V _{DDA} ≤ 2.7 V	-	0.8	2	
		2.7 V ≤ V _{DDA} ≤ 3.6 V	-	1.2	4	
V _{offset}	Comparator offset error		-	±4	±20	mV
dThreshold/dt	Threshold voltage temperature coefficient	V _{DDA} = 3.3V, T _A = 0 to 50 °C, V ₋ = V _{REFINT} , 3/4 V _{REFINT} , 1/2 V _{REFINT} , 1/4 V _{REFINT}	-	15	30	ppm / °C
I _{COMP2}	Current consumption ⁽³⁾	Fast mode	-	3.5	5	μA
		Slow mode	-	0.5	2	

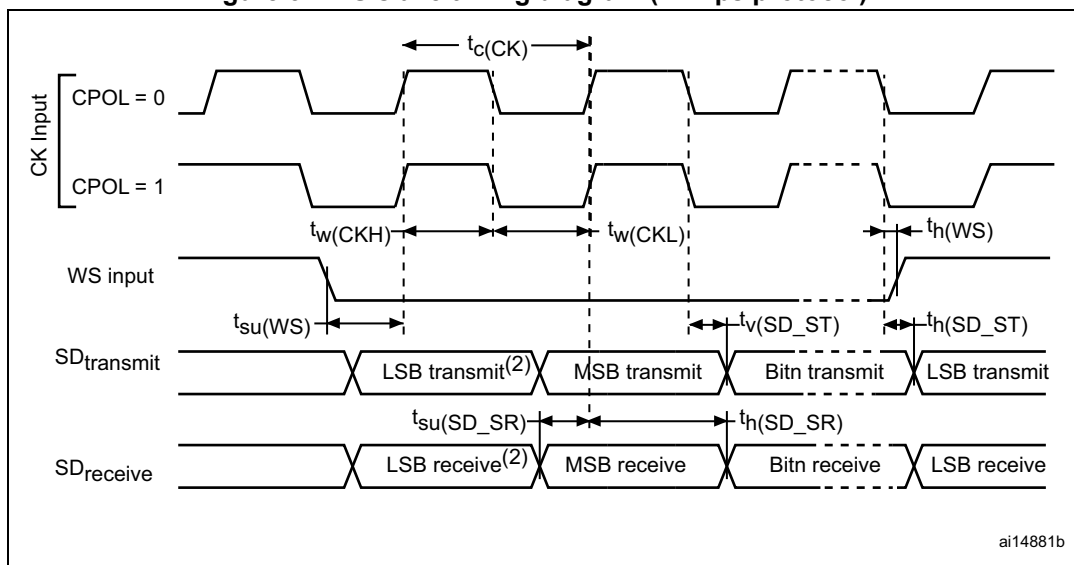
1. Guaranteed by characterization results.
2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
3. Comparator consumption only. Internal reference voltage (required for comparator operation) is not included.

Figure 35. SPI timing diagram - slave mode and CPHA = 1⁽¹⁾

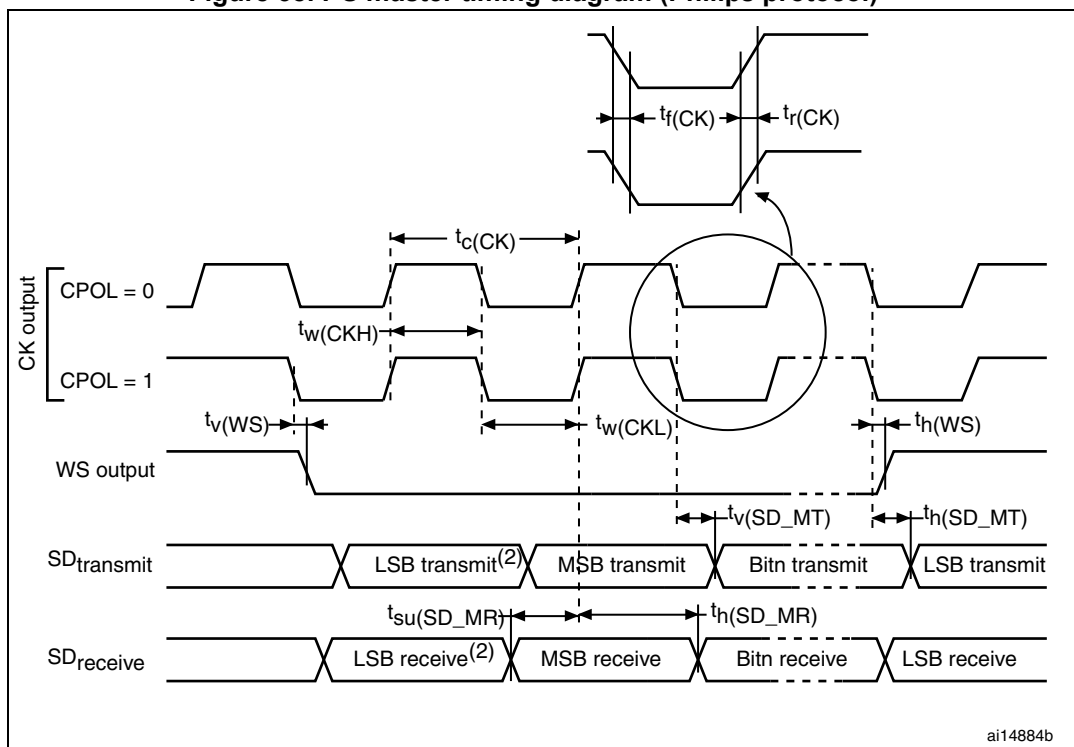
1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Figure 36. SPI timing diagram - master mode⁽¹⁾

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Figure 37. I²S slave timing diagram (Philips protocol)⁽¹⁾

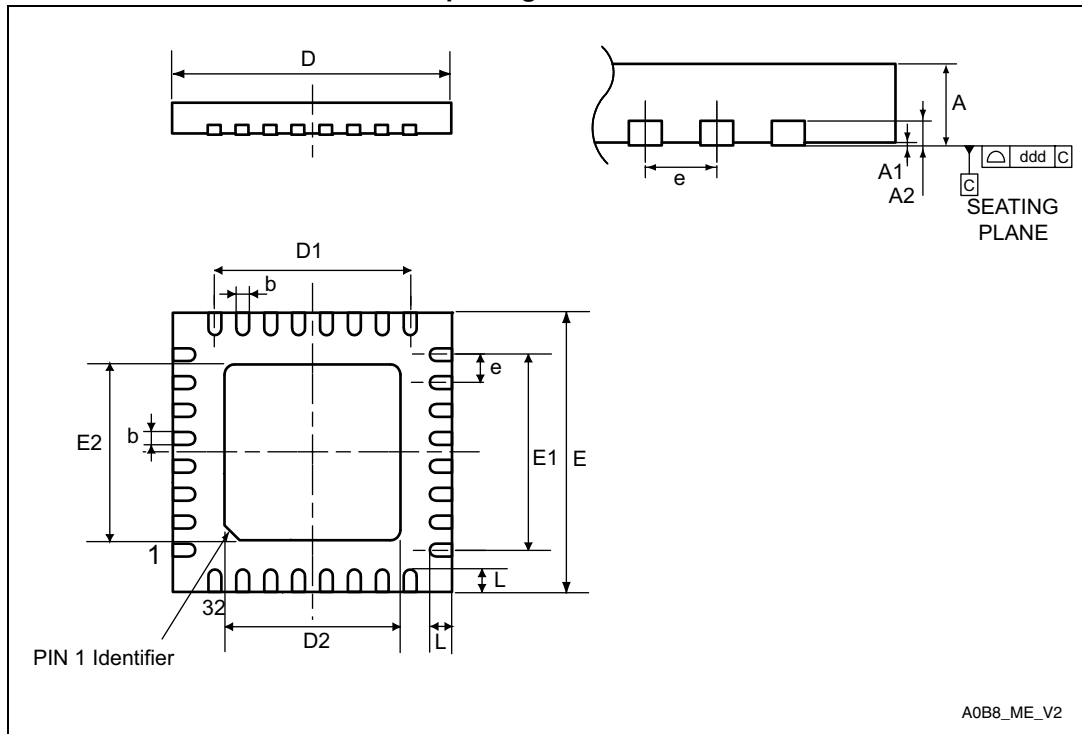
1. Measurement points are done at CMOS levels: $0.3 \times V_{DD}$ and $0.7 \times V_{DD}$.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 38. I²S master timing diagram (Philips protocol)⁽¹⁾

1. Guaranteed by characterization results.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

7.8 UFQFPN32 package information

Figure 59. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package outline

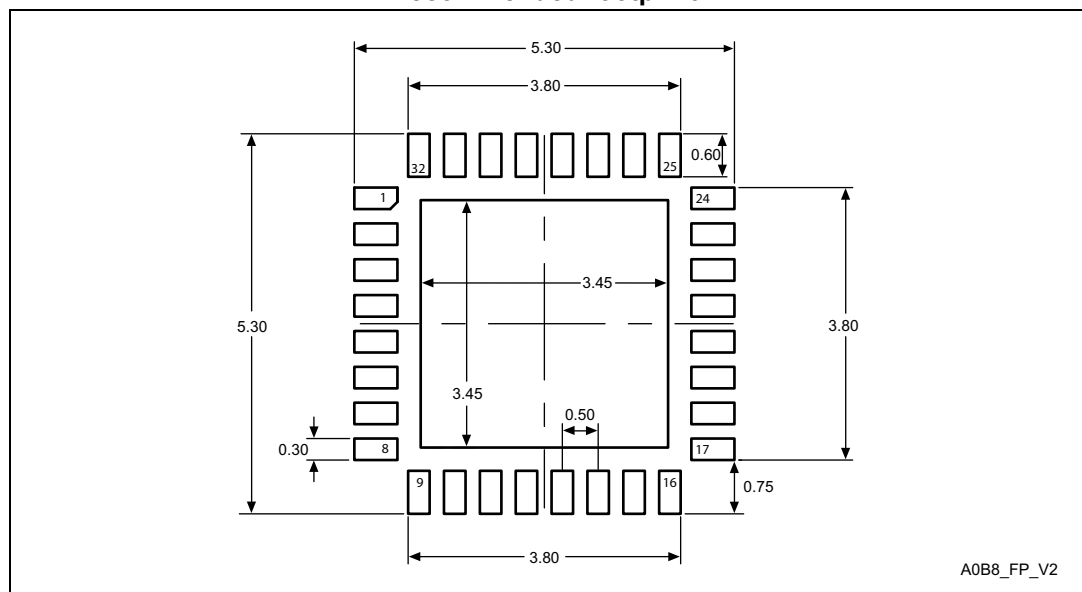


1. Drawing is not to scale.

Table 86. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.152	-	-	0.0060	-
b	0.180	0.230	0.280	0.0071	0.0091	0.0110
D	4.900	5.000	5.100	0.1929	0.1969	0.2008
D1	3.400	3.500	3.600	0.1339	0.1378	0.1417
D2	3.400	3.500	3.600	0.1339	0.1378	0.1417
E	4.900	5.000	5.100	0.1929	0.1969	0.2008
E1	3.400	3.500	3.600	0.1339	0.1378	0.1417
E2	3.400	3.500	3.600	0.1339	0.1378	0.1417
e	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 60. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat recommended footprint

1. Dimensions are expressed in millimeters.